Electronic Supplementary Information

Effects of Ge and Sn substitution on the metal-semiconductor transition and thermoelectric properties of $Cu_{12}Sb_4S_{13}$ tetrahedrite

Yasufumi Kosaka,[a] Koichiro Suekuni,*[b] Katsuaki Hashikuni,[a] Yohan Bouyrie,[c] Michihiro Ohta,[c] and Toshiro Takabatake[a,d]

[a] *Department of Quantum Matter, Graduate School of Advanced Sciences of Matter, Hiroshima University, Higashi-Hiroshima, 739-8530, Japan*

[b] *Department of Applied Science for Electronics and Materials, Interdisciplinary Graduate School of Engineering Sciences, Kyushu University, Kasuga, Fukuoka 816-8580, Japan*

** suekuni.koichiro.063@m.kyushu-u.ac.jp*

[c] *Research Institute for Energy Conservation, National Institute of Advanced Industrial Science and Technology (AIST), Tsukuba, Ibaraki 305-8568, Japan*

[d] *Institute for Advanced Materials Research, Hiroshima University, Higashi-Hiroshima, 739-8530, Japan*

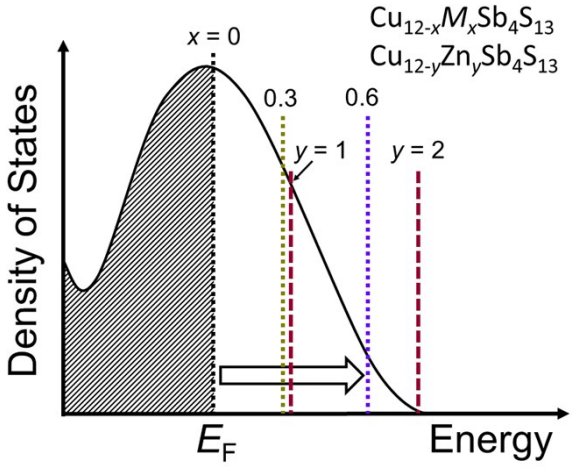

Fig. S1 Schematic picture of the density of states near the valence band top for $Cu_{12-x}M_xSb_4S_{13}$ (M = Ge, Sn) and $Cu_{12-y}Zn_ySb_4S_{13}$.

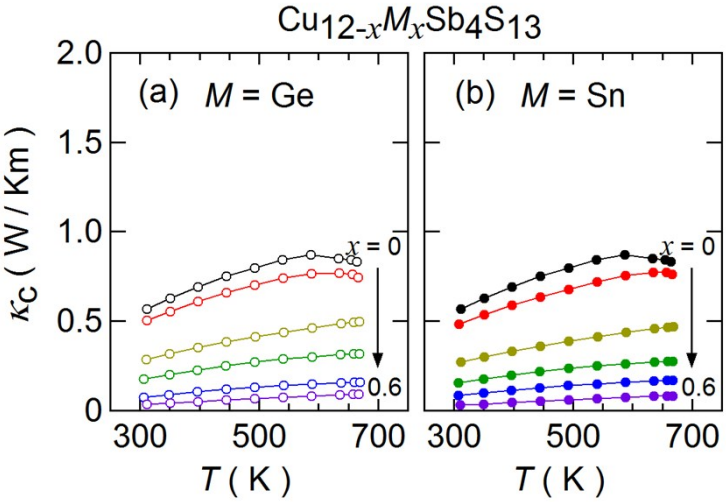

Fig. S2 Temperature dependence of charge carrier part of thermal conductivity κ_c for (a) M = Ge and (b) M = Sn of $Cu_{12-x}M_xSb_4S_{13}$ ($x \leq 0.6$).